

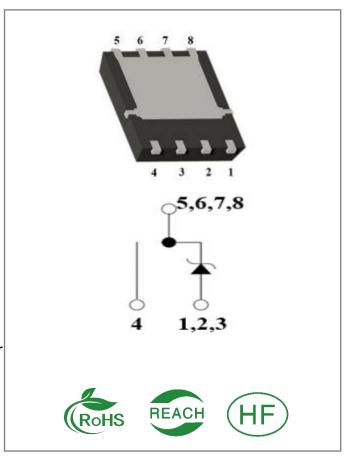
VRRM	IF ( TC=150°C)	QC	
650V	6A	17nC	

#### **Applications:**

- Power Factor Correction
- Sever Mode Power Supplies
- Uninterruptible Power Supply

#### **Features:**

- Low Forward Voltage Drop
- High-Speed Switching
- Positive Temperature Coefficient
- Temperature-Independent Switching Behavior



**Ordering Information** 

Part Number	Package	Marking	Packing	Qty.
RSS06065G	PDFN5*6	RSS06065G	Tape&reel	5000 PCS



# Maximum Ratings (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
VRRM	Repetitive Peak Reverse Voltage		V		
VRSM	Surge Peak Reverse Voltage	650	V		
VR DC Blocking Voltage		650	٧		
IF	IF Forward Current		Α	TC = 150°C	Fig.7
IFSM	FSM Non-Repetitive Forward Surge Current		Α	TC = 25°C, tp = 10ms Half Sine Wave	
IF,Max	Max Non-Repetitive Peak Forward Surge Current		Α	TC=25°C, tP= 10 μs, Pulse	
IFRM	Repetitive Peak Forward Surge Current	40	А	TC = $25^{\circ}$ C, tp = $10$ ms Half Sine Wave	
Ptot	Power Dissipation	111 48	W	TC = 25℃ TC = 110℃	Fig.6
TJ,TST G	Operating Junction and Storage Temperature	-55 to175	${\mathbb C}$		

# **Electrical Characteristics** (TJ= 25°C unless otherwise specified)

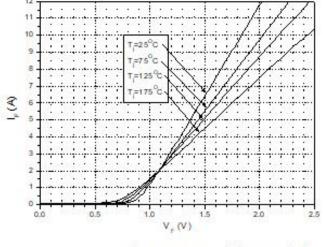
Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
VF	Forward Voltage	1.3 1.75	1.7 2.0	V	IF = 6A, TJ = 25°C IF = 6A, TJ = 175°C	Fig.1
IR	Reverse Current		10 200	μΑ	VR =650V, TJ = 25°C VR = 650V, TJ = 175°C	Fig.2
С	Total Capacitance	332 33 28	/	pF	VR=0V, TJ = $25^{\circ}$ C, f=1MHz VR=200V, TJ = $25^{\circ}$ C, f=1MHz VR=400V, TJ = $25^{\circ}$ C, f = 1MHz	Fig.3
QC	Total Capacitive Charge	17	/	nC	$VR = 400V, TJ = 25^{\circ}C$ $Qc = \int_{0}^{V_{R}} C(V) dV$	Fig.4
Ec	Capacitance Stored Energy	4.3	/	μЈ	VR =400V	Fig.5

### Thermal Characteristics (TJ= 25 ℃ unless otherwise specified)

Symbol	Parameter	Тур.	Unit	Note	
RθJC	Thermal Resistance from Junction to Case	1.95	°C/ <b>W</b>	Fig.8	



#### **Typical Feature Curve**



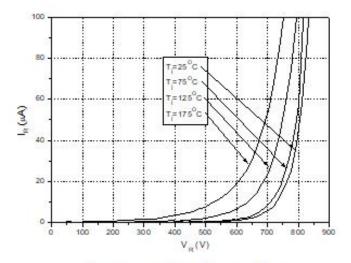
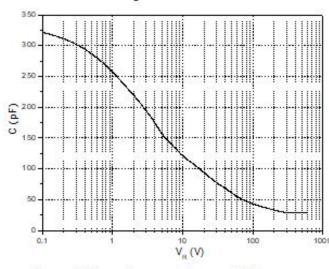


Figure 1.Forward Characteristics





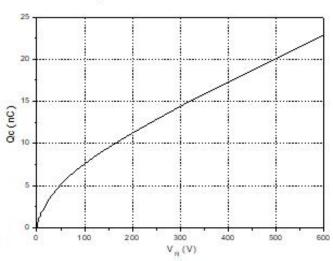
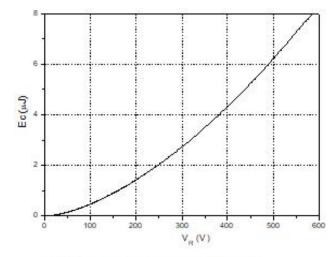


Figure 3.Capacitance vs. Reverse Voltage

Figure 4. Total Capacitance Charge vs. Reverse Voltage



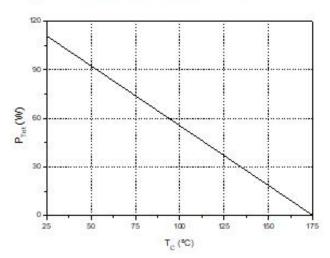


Figure 5. Capacitance Stored Energy

Figure 6. Power Derating



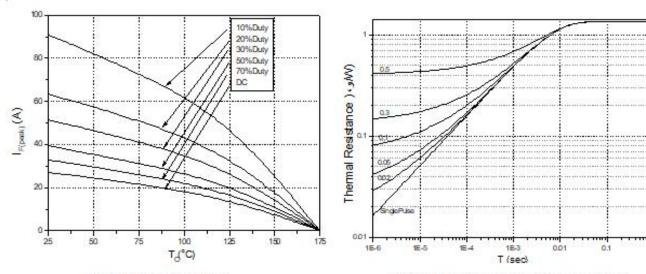
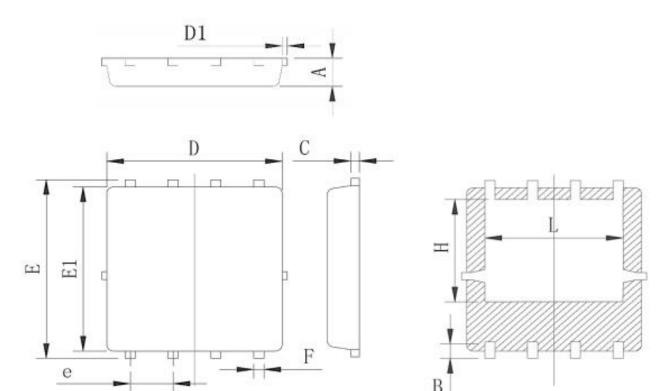


Figure 7. Current Derating

Figure 8. Transient Thermal Impedance



# Package outline drawing(PDFN5\*6 Unit: mm)



Symbol	Min	Тур	Max
A	0.90	0.95	1.00
В	0.48	0.58	0.68
C	0.20	0.254	0.30
D	5.00	5.20	5.40
D1			0.15
E	5.90	6.05	6.20
E1	5.40	5.55	5.70
e	1.22	1.27	1.32
F	0.25	0.30	0.35
Н	3.27	3.47	3.67
L	3.80	4.00	4.20



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